

### General Description

- Trench Power MOSFET technology
- Low  $R_{DS(ON)}$
- Low Gate Charge
- High Current Capability
- RoHS and Halogen-Free Compliant

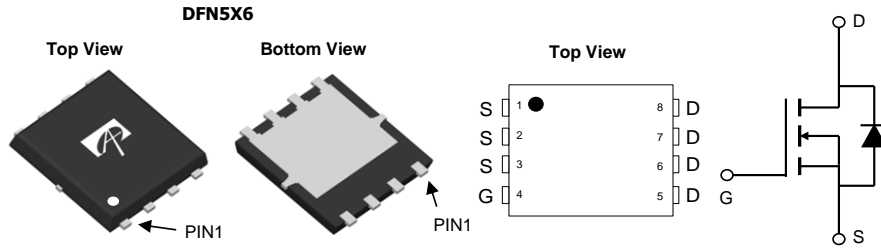
### Applications

- DC/DC Converters in Computing, Servers, and POL
- Isolated DC/DC Converters in Telecom and Industrial
- See Note I

### Product Summary

|                                  |                 |
|----------------------------------|-----------------|
| $V_{DS}$                         | 30V             |
| $I_D$ (at $V_{GS}=10V$ )         | 32A             |
| $R_{DS(ON)}$ (at $V_{GS}=10V$ )  | < 4.1m $\Omega$ |
| $R_{DS(ON)}$ (at $V_{GS}=4.5V$ ) | < 4.9m $\Omega$ |

100% UIS Tested  
 100% Rg Tested



| Orderable Part Number | Package Type | Form        | Minimum Order Quantity |
|-----------------------|--------------|-------------|------------------------|
| AONS36316             | DFN 5x6      | Tape & Reel | 3000                   |

### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

| Parameter                              | Symbol                                     | Maximum    | Units            |
|--|--|------------|------------------|
| Drain-Source Voltage                   | $V_{DS}$                                   | 30         | V                |
| Gate-Source Voltage                    | $V_{GS}$                                   | $\pm 12$   | V                |
| Continuous Drain Current <sup>G</sup>  | $T_C=25^\circ\text{C}$                     | 32         | A                |
|  | $T_C=100^\circ\text{C}$                    | 32         |                  |
| Pulsed Drain Current <sup>C</sup>      | $I_{DM}$                                   | 128        |                  |
| Continuous Drain Current               | $T_A=25^\circ\text{C}$                     | 28         | A                |
|  | $T_A=70^\circ\text{C}$                     | 22         |                  |
| Avalanche Current <sup>C</sup>         | $I_{AS}$                                   | 36         | A                |
| Avalanche energy                       | $L=0.01\text{mH}$ <sup>C</sup><br>$E_{AS}$ | 6          | mJ               |
| Power Dissipation <sup>B</sup>         | $T_C=25^\circ\text{C}$                     | 26         | W                |
|  | $T_C=100^\circ\text{C}$                    | 10         |                  |
| Power Dissipation <sup>A</sup>         | $T_A=25^\circ\text{C}$                     | 5          | W                |
|  | $T_A=70^\circ\text{C}$                     | 3.2        |                  |
| Junction and Storage Temperature Range | $T_J, T_{STG}$                             | -55 to 150 | $^\circ\text{C}$ |

### Thermal Characteristics

| Parameter                                  | Symbol          | Typ | Max | Units              |
|--|-----------------|-----|-----|--------------------|
| Maximum Junction-to-Ambient <sup>A</sup>   | $R_{\theta JA}$ | 20  | 25  | $^\circ\text{C/W}$ |
| Maximum Junction-to-Ambient <sup>A,D</sup> |                 | 45  | 55  | $^\circ\text{C/W}$ |
| Maximum Junction-to-Case                   | $R_{\theta JC}$ | 4   | 4.8 | $^\circ\text{C/W}$ |

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

| Symbol                      | Parameter                             | Conditions   | Min | Typ        | Max        | Units |
|-----------------------------|---------------------------------------|--|-----|------------|------------|-------|
| <b>STATIC PARAMETERS</b>    |                                       |  |     |            |            |       |
| BV <sub>DSS</sub>           | Drain-Source Breakdown Voltage        | I <sub>D</sub> =250μA, V <sub>GS</sub> =0V   | 30  |            |            | V     |
| I <sub>DSS</sub>            | Zero Gate Voltage Drain Current       | V <sub>DS</sub> =30V, V <sub>GS</sub> =0V<br>T <sub>J</sub> =55°C                          |     |            | 1<br>5     | μA    |
| I <sub>GSS</sub>            | Gate-Body leakage current             | V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V   |     |            | ±100       | nA    |
| V <sub>GS(th)</sub>         | Gate Threshold Voltage                | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA                                   | 1.1 | 1.5        | 1.9        | V     |
| R <sub>DS(ON)</sub>         | Static Drain-Source On-Resistance     | V <sub>GS</sub> =10V, I <sub>D</sub> =20A<br>T <sub>J</sub> =125°C                         |     | 3.4<br>4.7 | 4.1<br>5.7 | mΩ    |
|                             |                                       | V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A   |     | 3.9        | 4.9        | mΩ    |
| g <sub>FS</sub>             | Forward Transconductance              | V <sub>DS</sub> =5V, I <sub>D</sub> =20A   |     | 100        |            | S     |
| V <sub>SD</sub>             | Diode Forward Voltage                 | I <sub>S</sub> =1A, V <sub>GS</sub> =0V  |     | 0.7        | 1          | V     |
| I <sub>S</sub>              | Maximum Body-Diode Continuous Current |  |     |            | 30         | A     |
| <b>DYNAMIC PARAMETERS</b>   |                                       |  |     |            |            |       |
| C <sub>iss</sub>            | Input Capacitance                     | V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz  |     | 2005       |            | pF    |
| C <sub>oss</sub>            | Output Capacitance                    |  |     | 430        |            | pF    |
| C <sub>rss</sub>            | Reverse Transfer Capacitance          |  |     | 50         |            | pF    |
| R <sub>g</sub>              | Gate resistance                       | f=1MHz   | 1.1 | 2.2        | 3.3        | Ω     |
| <b>SWITCHING PARAMETERS</b> |                                       |  |     |            |            |       |
| Q <sub>g</sub> (10V)        | Total Gate Charge                     | V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =20A                            |     | 30         | 42         | nC    |
| Q <sub>g</sub> (4.5V)       | Total Gate Charge                     |  |     | 13.5       | 19         | nC    |
| Q <sub>gs</sub>             | Gate Source Charge                    |  |     | 5.5        |            | nC    |
| Q <sub>gd</sub>             | Gate Drain Charge                     |  |     | 3.5        |            | nC    |
| t <sub>D(on)</sub>          | Turn-On DelayTime                     | V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, R <sub>L</sub> =0.75Ω,<br>R <sub>GEN</sub> =3Ω |     | 8          |            | ns    |
| t <sub>r</sub>              | Turn-On Rise Time                     |  |     | 3          |            | ns    |
| t <sub>D(off)</sub>         | Turn-Off DelayTime                    |  |     | 34         |            | ns    |
| t <sub>f</sub>              | Turn-Off Fall Time                    |  |     | 5.5        |            | ns    |
| t <sub>rr</sub>             | Body Diode Reverse Recovery Time      | I <sub>F</sub> =20A, di/dt=500A/μs   |     | 12         |            | ns    |
| Q <sub>rr</sub>             | Body Diode Reverse Recovery Charge    | I <sub>F</sub> =20A, di/dt=500A/μs   |     | 21         |            | nC    |

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The Power dissipation P<sub>DSM</sub> is based on R<sub>θJA</sub> ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature T<sub>J(MAX)</sub>=150° C.

D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to case R<sub>θJC</sub> and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150° C. The SOA curve provides a single pulse rating.

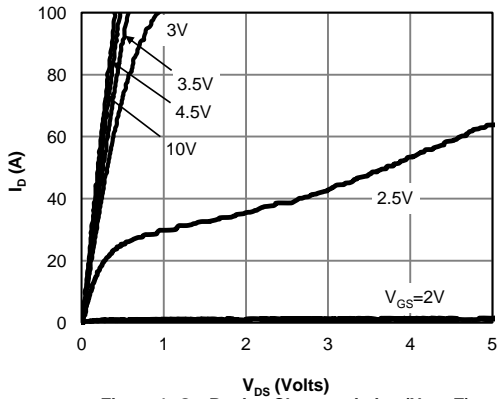
G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C.

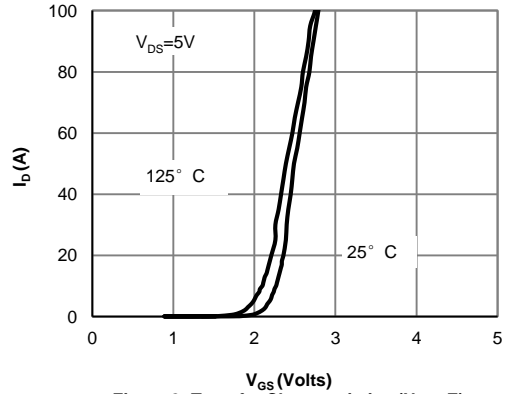
I. For application requiring slow >1ms turn-on/turn-off, please consult AOS FAE for proper product selection.

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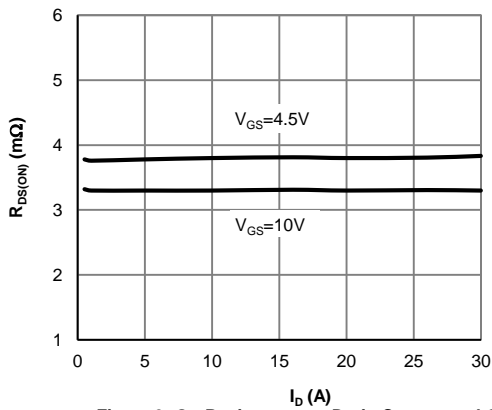
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



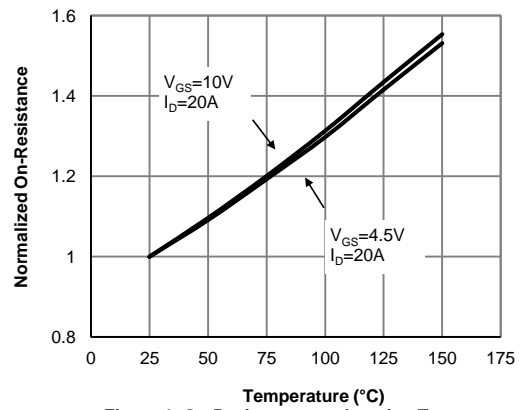
**Figure 1: On-Region Characteristics (Note E)**



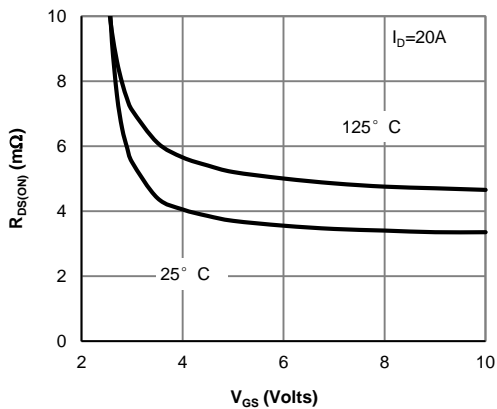
**Figure 2: Transfer Characteristics (Note E)**



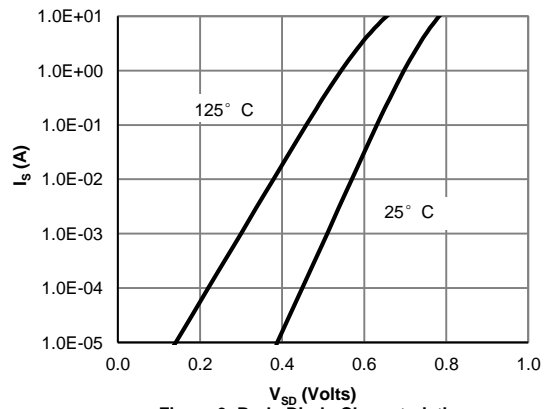
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)**



**Figure 4: On-Resistance vs. Junction Temperature (Note E)**

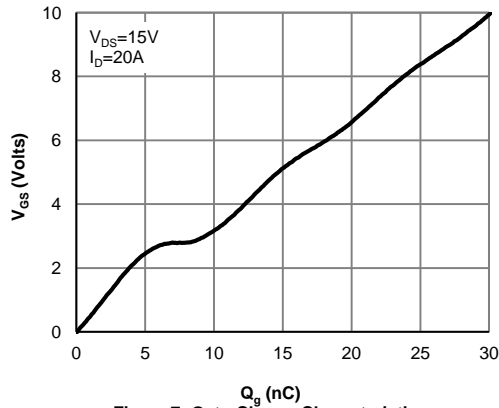


**Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)**

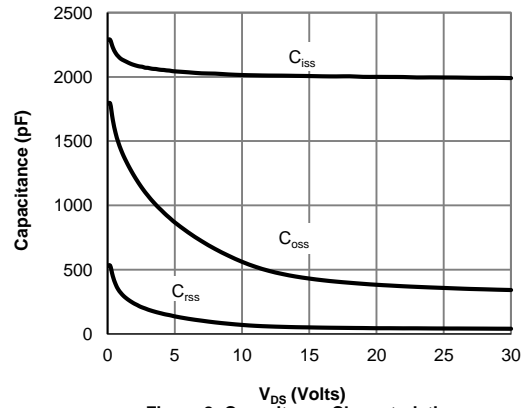


**Figure 6: Body-Diode Characteristics (Note E)**

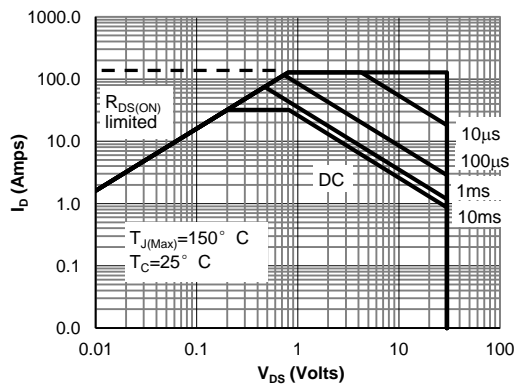
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



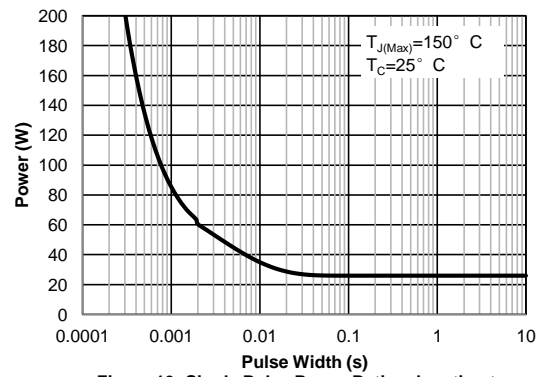
**Figure 7: Gate-Charge Characteristics**



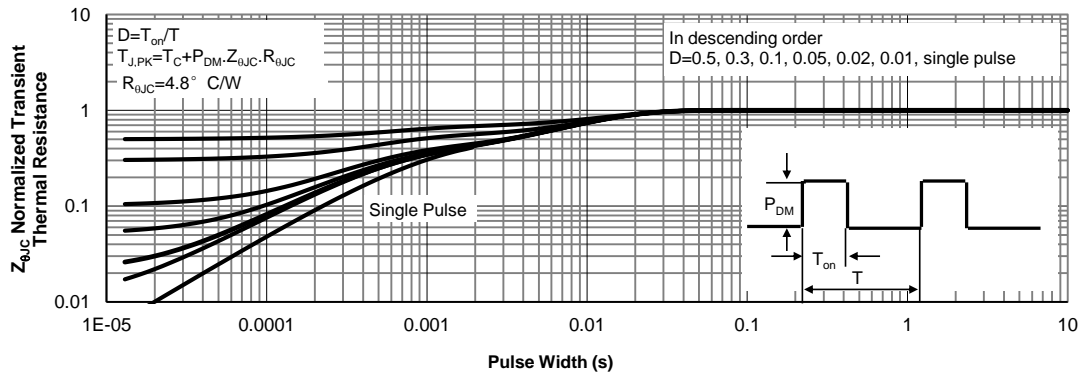
**Figure 8: Capacitance Characteristics**



**Figure 9: Maximum Forward Biased Safe Operating Area (Note F)**



**Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)**



**Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)**

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

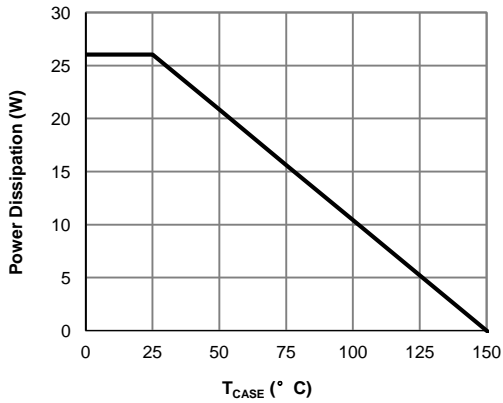


Figure 12: Power De-rating (Note F)

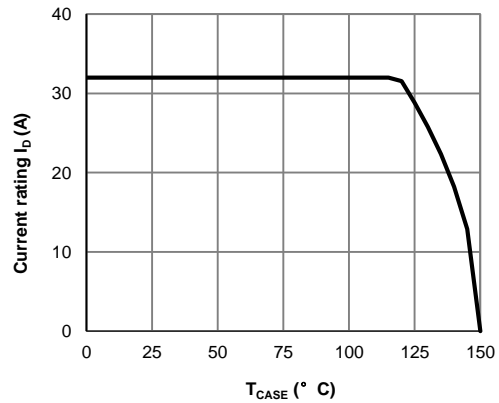


Figure 13: Current De-rating (Note F)

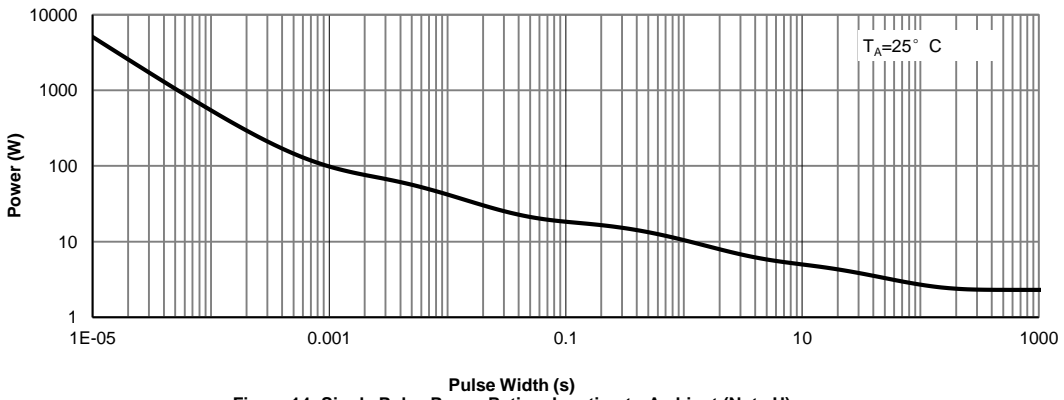


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

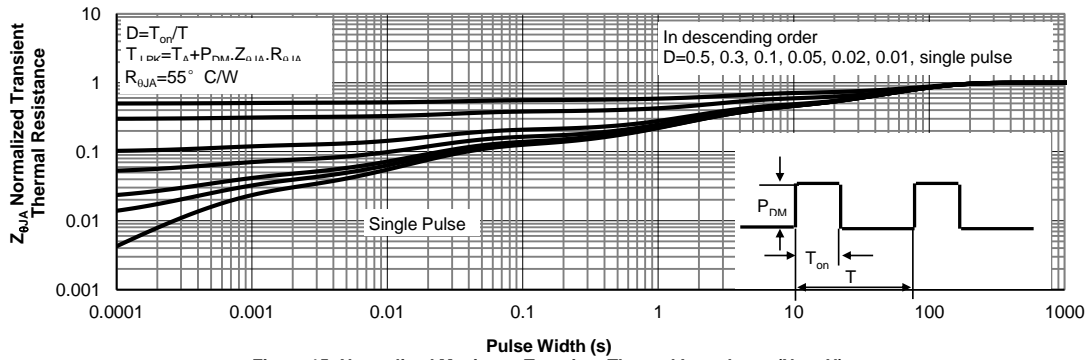


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

Figure A: Gate Charge Test Circuit & Waveforms

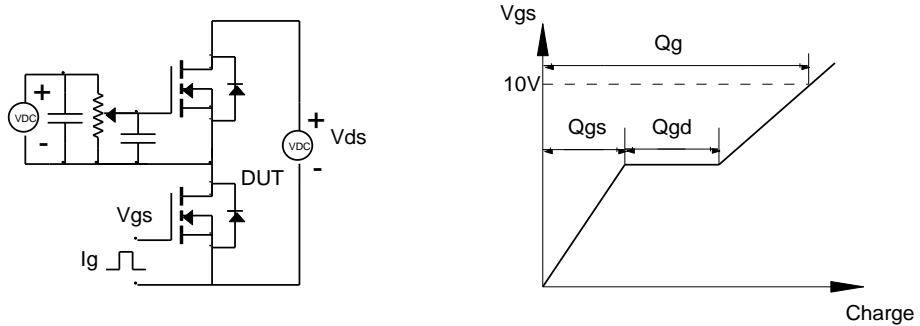


Figure B: Resistive Switching Test Circuit & Waveforms

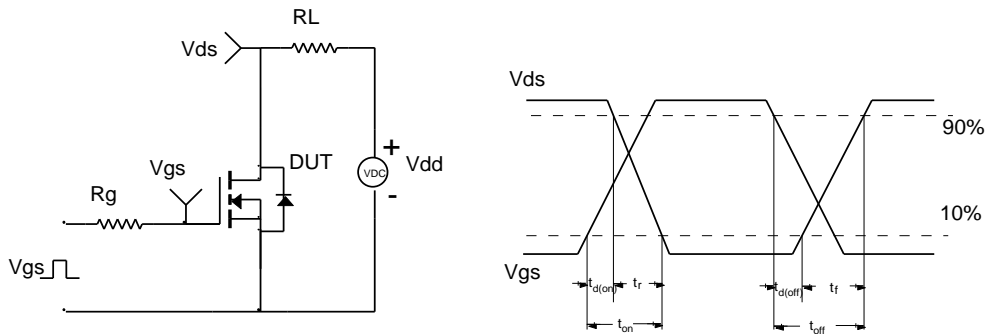


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

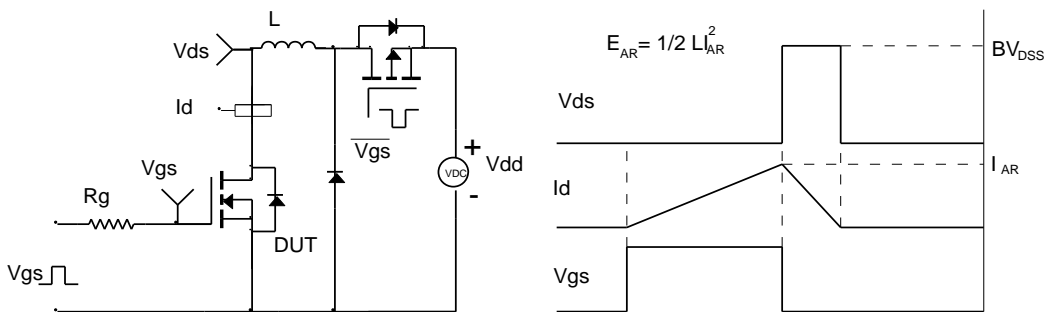
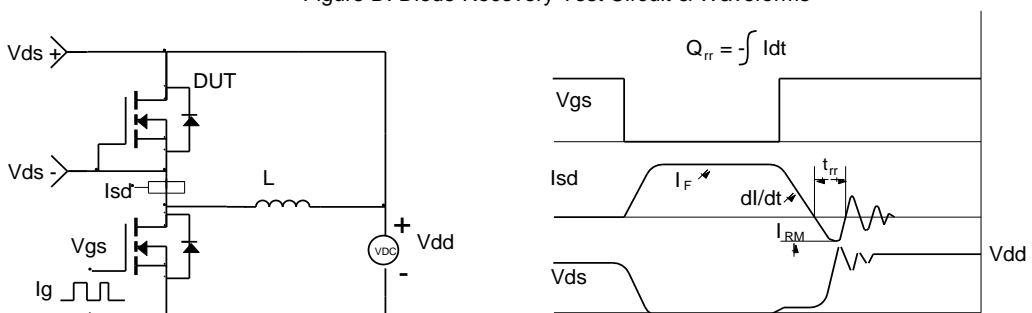


Figure D: Diode Recovery Test Circuit & Waveforms



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